

BC369 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

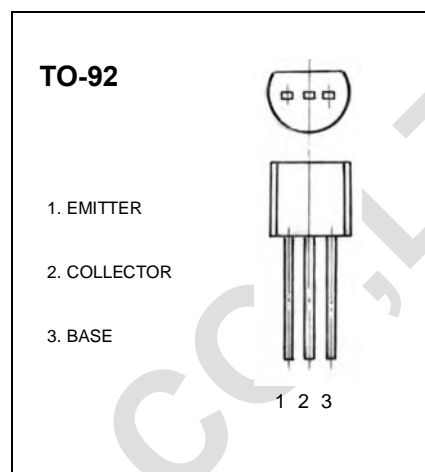
$$I_{CM}: -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -25 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-25		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -25\text{V}, I_E = 0$		-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$		-10	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -0.5\text{mA}$	85	375	
Collector-emitter voltage	$V_{CE(sat)}$	$I_C = -1\text{A}, I_B = -100\text{mA}$		-0.5	V
Base-emitter voltage	$V_{BE(on)}$	$I_C = -1\text{A}, V_{CE} = -1\text{V}$		-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 20\text{MHz}$	65		MHz